## NSN 5961-01-006-8435

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-006-8435 **Inclosure Material:** Metal **Overall Length:** 0.450 inches **Overall Diameter:** 0.667 inches **Mounting Facility Quantity: Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.667 inches and 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 15.8 breakdown voltage, dc **Current Rating Per Characteristic:** 3170.00 milliamperes repetitive peak forward current **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius case **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 1 tab, solder lug **Specification Data:** 81349-mil-s-19500/358 government specification Shelf Life: N/a **Unit Of Measure:** 

Fiig: A110a0

No

**Demilitarization:**